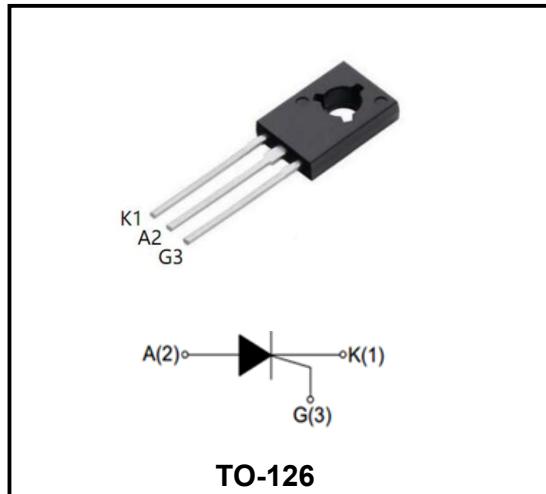


## 4.0A Sensitive Gate SCRs

### Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	4.0	A
$V_{DRM} V_{RRM}$	600/800	V
$I_{GT}$	200	uA



### Features

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

### Application

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on

### Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	$V_{DRM}$	600/800	V
Repetitive peak reverse voltage	$V_{RRM}$	600/800	V
RMS on-state current	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	$I_{TSM}$	30	A
$I^2t$ value for fusing ( $t_p=10ms$ )	$I^2t$	4.5	$A^2s$
Critical rate of rise of on-state current ( $ G  = 2 \times  G_T $ )	$dI_T/dt$	50	$A/us$
Peak gate current	$I_{GM}$	1.2	A
Average gate power dissipation	$P_G (AV)$	0.2	W
Junction Temperature	$T_J$	-40~+110	°C
Storage Temperature	$T_{STG}$	-40 ~+150	°C

## Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Gate trigger current	I <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =140Ω, Fig. 6	10	-	200	μA
Gate trigger voltage	V <sub>GT</sub>	V <sub>D</sub> =12V, R <sub>L</sub> =140Ω, T <sub>j</sub> =25°C	-	0.65	0.8	V
Non-triggering gate voltage	V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>GGK</sub> =1kΩ, R <sub>L</sub> =3.3kΩ, T <sub>j</sub> =110°C	0.2	-	-	V
Holding current	I <sub>H</sub>	I <sub>T</sub> =50mA, R <sub>GGK</sub> =1kΩ, T <sub>j</sub> =25°C, Fig. 6	-	-	5	mA
Latching current	I <sub>L</sub>	I <sub>G</sub> =1mA, R <sub>GGK</sub> =1kΩ, T <sub>j</sub> =25°C, Fig. 6	-	-	6	mA
Critical-rate of rise of commutation voltage	dV <sub>D</sub> /dt	V <sub>D</sub> =2/3V <sub>DRM</sub> , R <sub>GGK</sub> =1kΩ, T <sub>j</sub> =110°C	10	-	-	V/μs

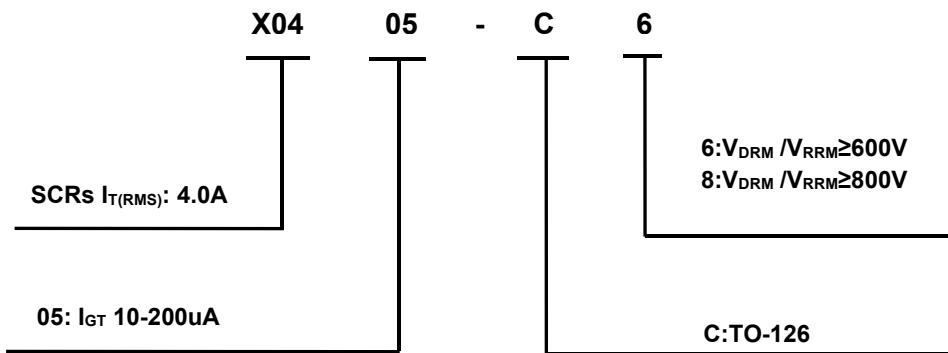
## STATIC CHARACTERISTICS

On-state Voltage	V <sub>TM</sub>	I <sub>TM</sub> =8A, t <sub>p</sub> =380μs, Fig. 4	-	-	1.55	V
Repetitive Peak Off-State Current	I <sub>DRM</sub>	V <sub>D</sub> =V <sub>DRM</sub> = V <sub>RRM</sub>	T <sub>j</sub> =25°C	-	5	μA
Repetitive Peak Reverse Current	I <sub>RRM</sub>		T <sub>j</sub> =110°C	-	150	μA

## THERMAL RESISTANCES

Thermal resistance	R <sub>th</sub> (j-c)	Junction to case	TYP.	7.2	°C/W
	R <sub>th</sub> (j-a)	Junction to ambient	TYP.	100	°C/W

## Ordering Information



## Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on state current (full cycle)

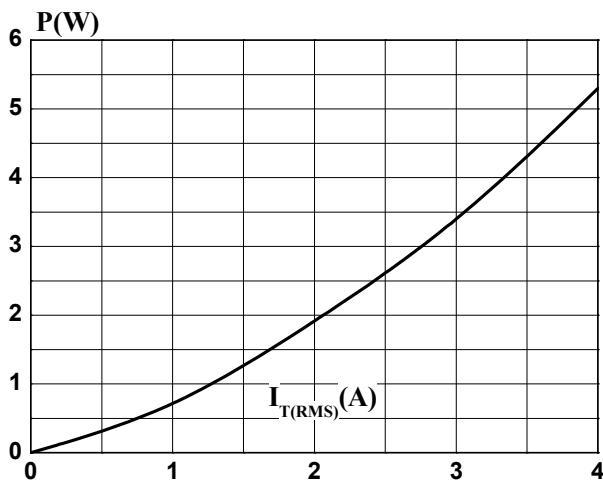


FIG.2: RMS on-state current versus case temperature (full cycle)

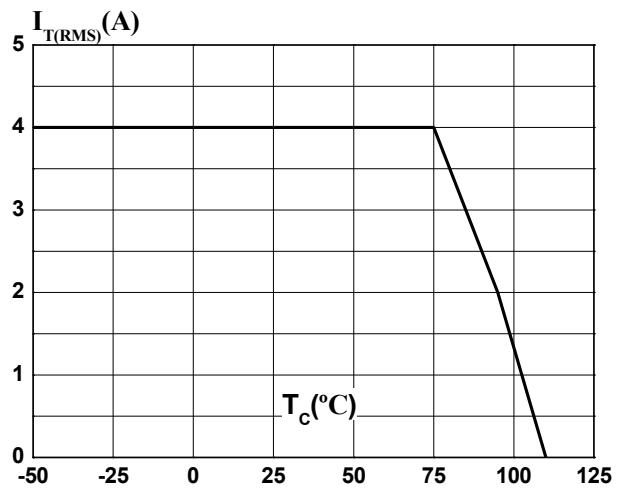


FIG.3: Surge peak on-state current versus number of cycles

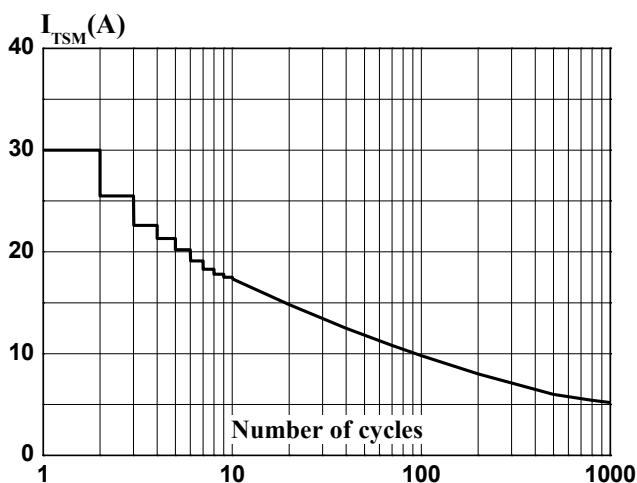


FIG.4: On-state characteristics (maximum values)

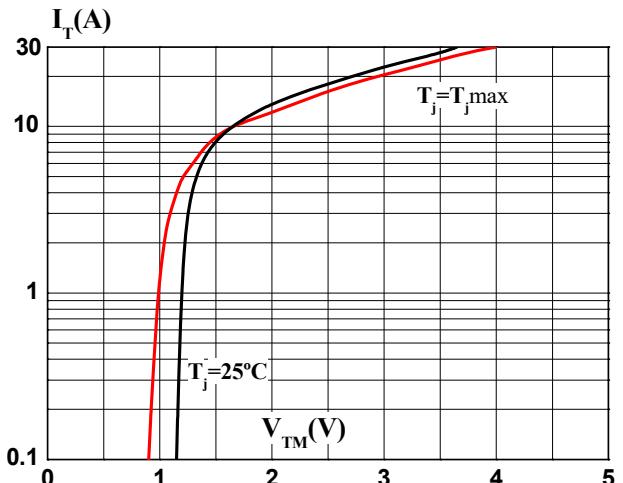


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10ms$

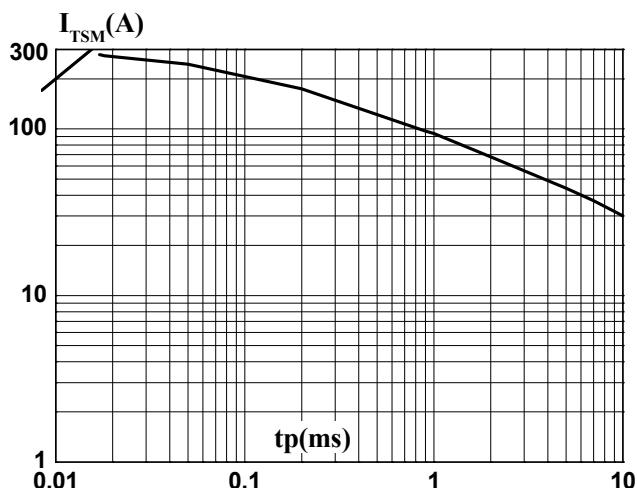
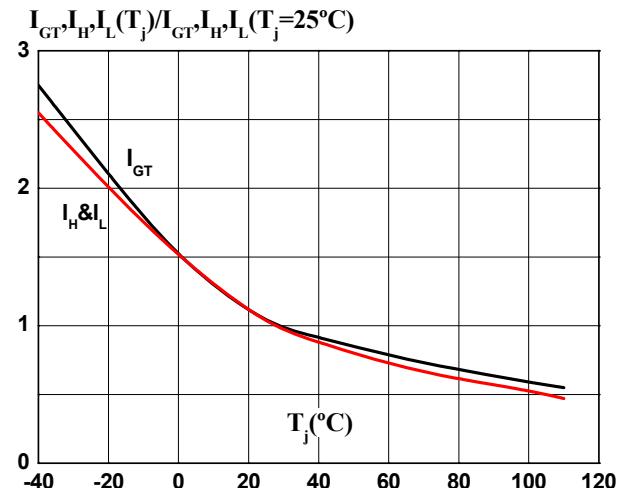


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



**Ordering information**

Package	Packing Description	Base Quantity
TO-126	Bulk	500pcs/Bag

**Package Dimensions**

TO-126

Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.80	0.094	0.110
A1	1.00	1.40	0.039	0.055
b	0.66	0.86	0.026	0.034
b1	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
D	7.30	7.70	0.287	0.303
E	10.60	11.00	0.417	0.433
e	2.25	2.33	0.089	0.092
e1	4.50	4.66	0.177	0.183
L	14.00	15.00	0.551	0.591
L1	1.90	2.50	0.075	0.098
Φ	3.10	3.30	0.122	0.130

The technical drawing illustrates the physical dimensions of the TO-126 package. The top view shows the overall width D, height L, lead spacing b, lead thickness e, and lead pitch Φ. The side view shows the lead height L1, lead thickness e1, and the distance from the lead center to the case A1. The front view shows the lead thickness e and the lead pitch Φ. Reference dimensions L2 and L3 are also indicated.

## Disclaimer

The information presented in this document is for reference only. GuangDong Youfeng Microelectronics Co.,Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise. The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices). YFW or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale. This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <https://www.yfwdiode.com>, or consult YFW sales office for further assistance.